

Description

The IRFR120NPbF uses advanced trench technology and

design to provide excellent R_{DS(ON)} with low gate charge.

It can be used in a wide variety of applications.

General Features

 $V_{DS} = 100V, I_{D} = 10A$

 $R_{DS(ON)}$ <160m Ω @ V_{GS} =10V

 $R_{DS(ON)}$ <170m Ω @ V_{GS} =4.5V

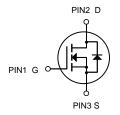
High density cell design for ultra low Rdson

Fully characterized avalanche voltage and current

Excellent package for good heat dissipation



TO-252-2L



N-Channel MOSFET

Application

Power switching application

Hard switched and high frequency circuits

Uninterruptible power supply

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
IRFR120NPbF	TO-252-2L	HXY MOSFET	2500

Absolute Maximum Ratings (T_A=25 ℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	100	V
Gate-Source Voltage	V _G s	±20	V
Drain Current-Continuous	ID	10	А
Drain Current-Pulsed (Note 1)	Ідм	20	А
Maximum Power Dissipation	P _D	40	W
Operating Junction and Storage Temperature Range	Тյ,Тѕтс	-55 To 175	$^{\circ}$
Thermal Resistance,Junction-to-Case (Note 2)	Rejc	3.75	°C/W



Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit	
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	100	-	-	V	
Zero Gate Voltage Drain Current	Ipss	V _{DS} =100V,V _{GS} =0V	-	1	1	μΑ	
Gate-Body Leakage Current	Igss	V _{GS} =±12V,V _{DS} =0V	-	-	±100	nA	
Gate Threshold Voltage	V _G S(th)	V _{DS} =V _{GS} ,I _D =250µA	1.0		2.5	V	
		V _{GS} =10V, I _D =3A -		140	160		
Drain-Source On-State Resistance	Rds(on)	V _{GS} =4.5V, I _D =3A	-	160	170	mΩ	
Forward Transconductance	grs	V _{DS} =5V,I _D =3A	-	5	-	S	
Input Capacitance	Clss		-	650	-	PF	
Output Capacitance	Coss	$V_{DS}=50V, V_{GS}=0V,$	-	25	-	PF	
Reverse Transfer Capacitance	Crss	F=1.0MHz	-	20	-	PF	
Turn-on Delay Time	td(on)		-	6	-	nS	
Turn-on Rise Time	t _r	V_{DD} =50V, R_L =19 Ω	-	4	-	nS	
Turn-Off Delay Time	td(off)	V_{GS} =10 V , R_{G} =3 Ω	-	20	-	nS	
Turn-Off Fall Time	t _f		-	4	-	nS	
Total Gate Charge	Qg		-	20.6		nC	
Gate-Source Charge	Qgs	$V_{DS}=50V,I_{D}=3A,$	-	2.1	-	nC	
Gate-Drain Charge	Q _{gd}	V _{GS} =10V	-	3.3	-	nC	
Diode Forward Voltage (Note 3)	Vsp	V _{GS} =0V,I _S =3A	-	-	1.2	V	
Diode Forward Current (Note 2)	Is		-	-	7	Α	

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- **3.** Pulse Test: Pulse Width ≤ 300μ s, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



Typical Electrical and Thermal Characteristics (Curves)

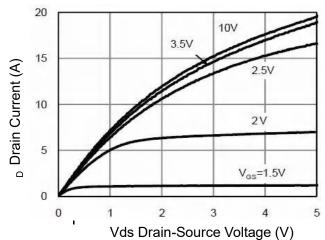


Figure 1 Output Characteristics

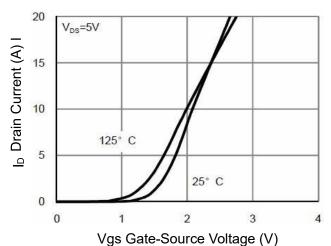


Figure 2 Transfer Characteristics

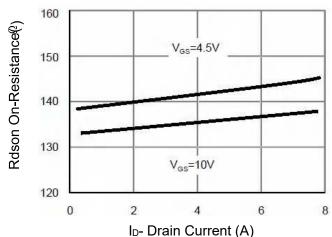


Figure 3 Rdson-Drain Current

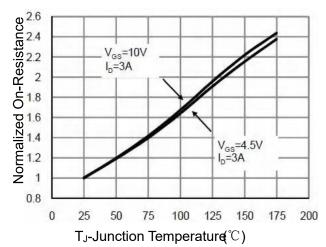


Figure 4 Rdson-Junction Temperature

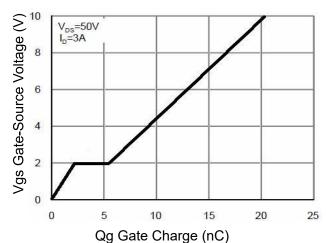


Figure 5 Gate Charge

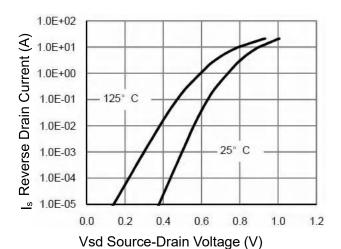
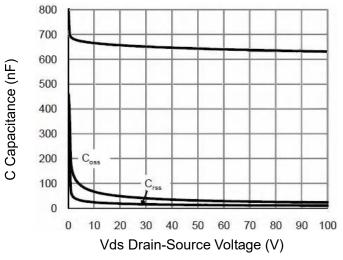


Figure 6 Source- Drain Diode Forward

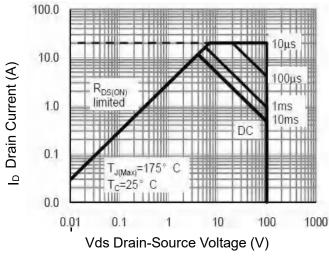




12 10 ID Drain Current (A) 8 6 4 2 0 0 25 50 75 100 125 150 T_J-Junction Temperature(°C)

Figure 7 Capacitance vs Vds

Figure 9 BV_{DSS} vs Junction Temperature



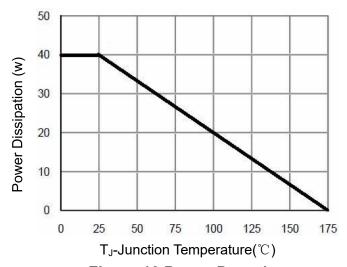
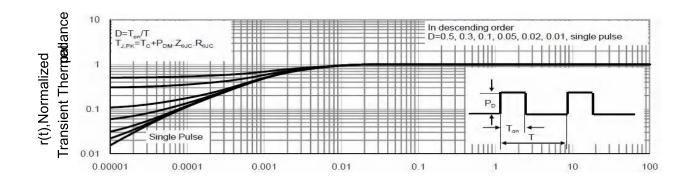


Figure 8 Safe Operation Area

Figure 10 Power De-rating

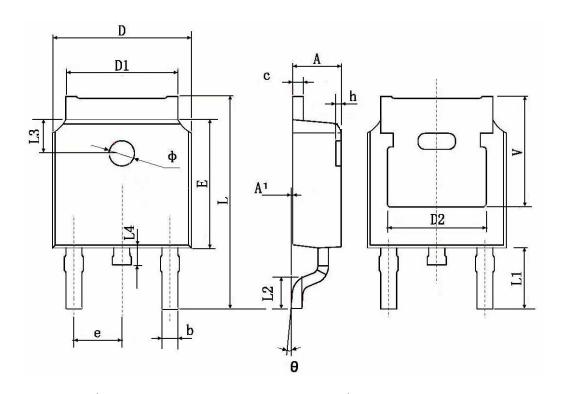


Square Wave Pluse Duration(sec)

Figure 11 Normalized Maximum Transient Thermal Impedance



TO-252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches			
	Min.	Max.	Min.	Max.		
Α	2.200	2.400	0.087	0.094		
A1	0.000	0.127	0.000	0.005		
b	0.660	0.860	0.026	0.034		
С	0.460	0.580	0.018	0.023		
D	6.500	6.700	0.256	0.264		
D1	5.100	5.460	0.201	0.215		
D2	0.483 TYP.		0.190 TYP.			
Е	6.000	6.200	0.236	0.244		
е	2.186	2.386	0.086	0.094		
L	9.800	10.400	0.386	0.409		
L1	2.900	2.900 TYP.		0.114 TYP.		
L2	1.400	1.700	0.055	0.067		
L3	1.600 TYP.		0.063 TYP.			
L4	0.600	1.000	0.024	0.039		
Ф	1.100	1.300	0.043	0.051		
θ	0°	8°	0°	8°		
h	0.000	0.300	0.000	0.012		
V	5.350 TYP.		0.211 TYP.			



Attention

- Any and all HUA XUAN YANG ELECTRONICS products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your HUA XUAN YANG ELECTRONICS representative nearest you before using any HUA XUAN YANG ELECTRONICS products described or contained herein in such applications.
- HUA XUAN YANG ELECTRONICS assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all HUA XUAN YANG ELECTRONICS products described or contained herein.
- Specifications of any and all HUA XUAN YANG ELECTRONICS products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.
- HUA XUAN YANG ELECTRONICS CO.,LTD. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.
- In the event that any or all HUA XUAN YANG ELECTRONICS products(including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.
- No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of HUA XUAN YANG ELECTRONICS CO.,LTD.
- Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production.

 HUA XUAN YANG ELECTRONICS believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.
- Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the HUA XUAN YANG ELECTRONICS product that you intend to use.